

NCE Automotive N-Channel Super Trench Power MOSFET

Description

The NCEAP40T20AD uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

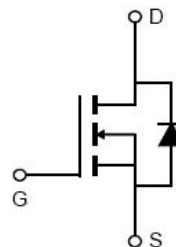
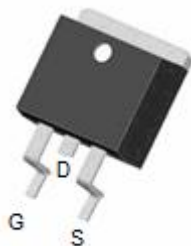
Application

- Automotive application
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

- $V_{DS} = 40V, I_D = 295A$
 $R_{DS(ON)} = 1.3m\Omega$, typical@ $V_{GS} = 10V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- Pb-free lead plating
- 175°C operating temperature
- 100% UIS tested
- 100% ΔV_{ds} tested
- **AEC-Q101 qualified**

TO-263



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AP40T20AD	NCEAP40T20AD	TO-263-2L	-	-	-

Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	295	A
Drain Current-Continuous($T_c = 100^\circ C$)	$I_D(100^\circ C)$	208	A
Pulsed Drain Current	I_{DM}	1180	A
Maximum Power Dissipation	P_D	270	W
Derating factor		1.8	W/°C
Single pulse avalanche energy (Note 1)	E_{AS}	1692	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.56	°C/W
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Electrical Characteristics ($T_c = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	1.3	1.6	m Ω
Gate resistance	R_G	$F=1.0MHz$	-	5	-	Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=20A$	-	90	-	S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=20V, V_{GS}=0V,$ $F=1.0MHz$	-	5834.6	-	pF
Output Capacitance	C_{oss}		-	2320.5	-	pF
Reverse Transfer Capacitance	C_{riss}		-	70	-	pF
Switching Characteristics (Note 2)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=20V, I_D=20A$ $V_{GS}=10V, R_G=1.6\Omega$	-	14.5	-	nS
Turn-on Rise Time	t_r		-	8	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	58	-	nS
Turn-Off Fall Time	t_f		-	10	-	nS
Total Gate Charge	Q_g	$V_{DS}=20V, I_D=20A,$ $V_{GS}=10V$	-	91	-	nC
Gate-Source Charge	Q_{gs}		-	29.4	-	nC
Gate-Drain Charge	Q_{gd}		-	19	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=20A$	-	-	1.2	V
Diode Forward Current	I_S		-	-	295	A
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ C, I_F = I_S$	-	-	38	nS
Reverse Recovery Charge	Q_{rr}	$di/dt = 100A/\mu s$ (Note3)	-	-	125	nC

Notes:

1. EAS condition : $T_J=25^\circ C, V_{DD}=20V, V_G=10V, L=0.5mH, R_g=25\Omega$
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}=175^\circ C$. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics

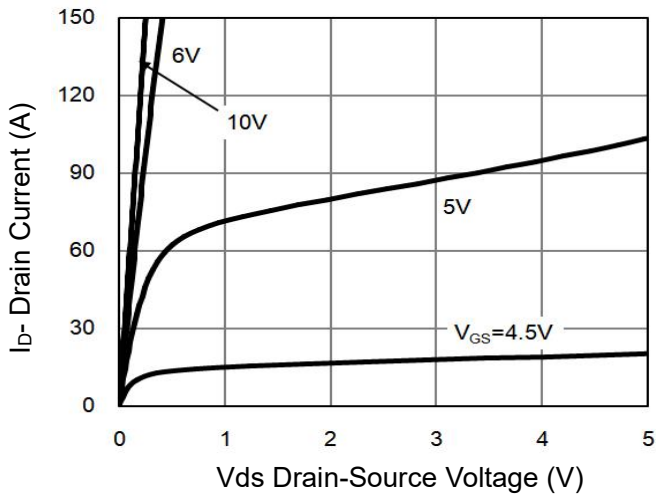


Figure 1 Output Characteristics

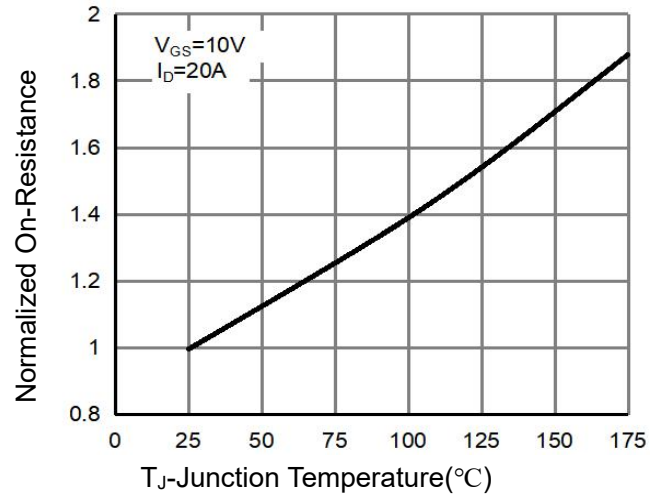


Figure 4 R_{dson} -Junction Temperature

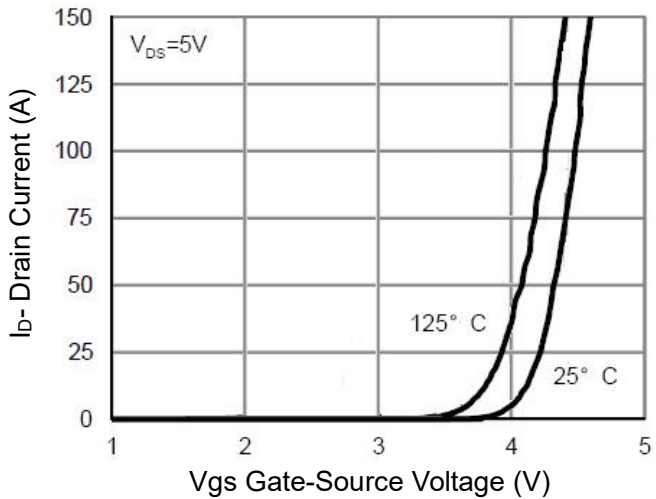


Figure 2 Transfer Characteristics

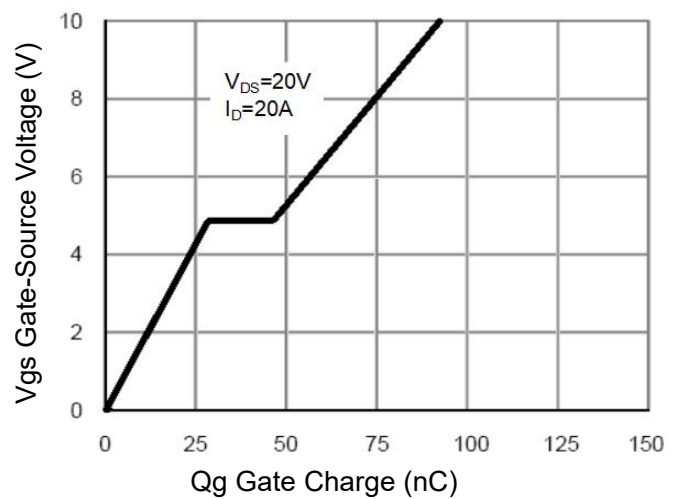


Figure 5 Gate Charge

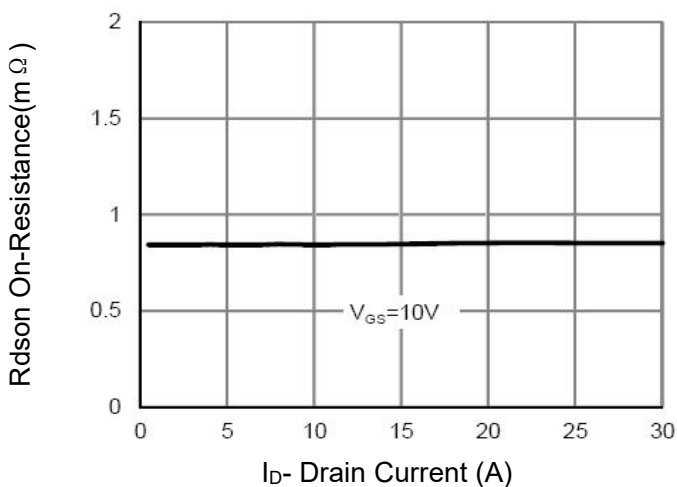


Figure 3 R_{dson} - Drain Current

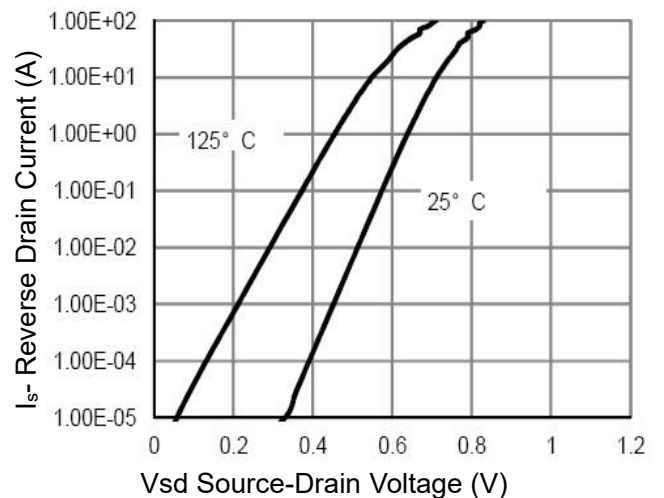


Figure 6 Source- Drain Diode Forward

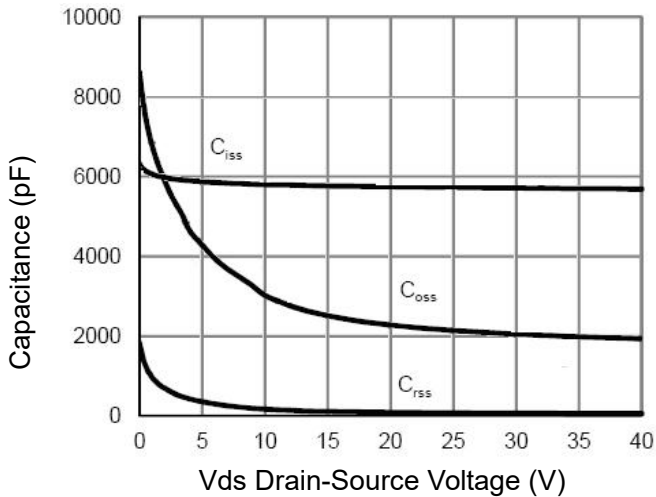


Figure 7 Capacitance vs Vds

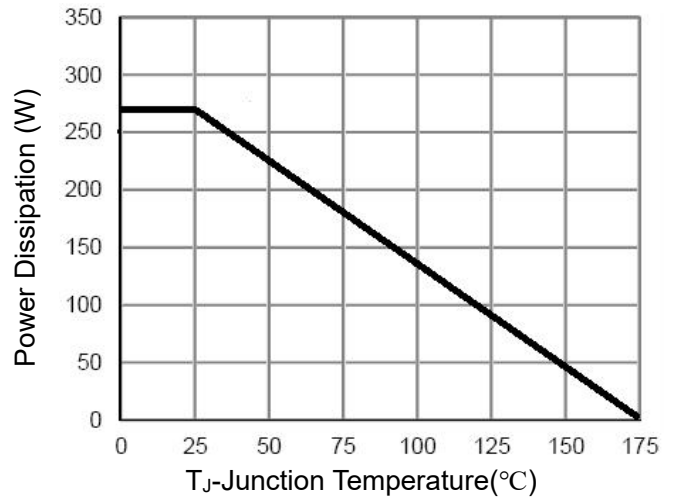


Figure 9 Power De-rating

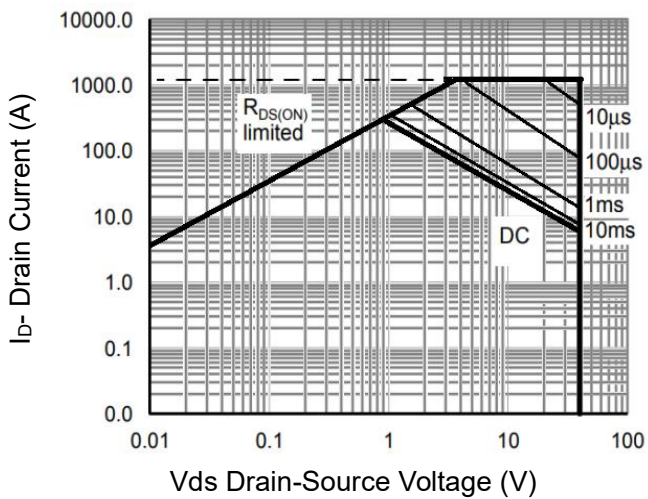


Figure 8 Safe Operation Area (Note 3)

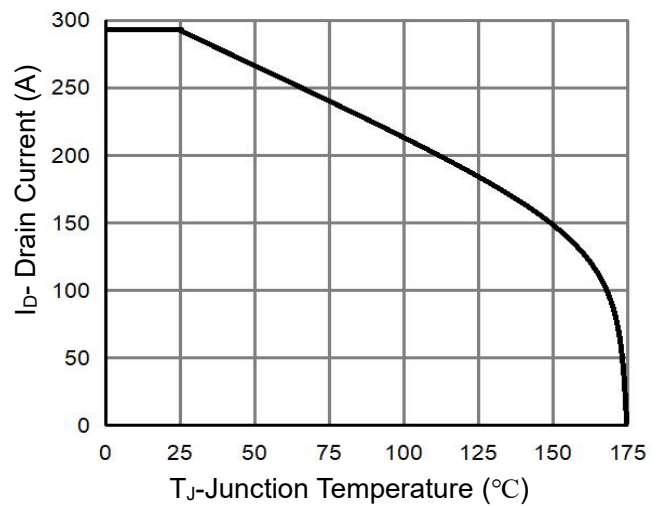


Figure 10 Current De-rating

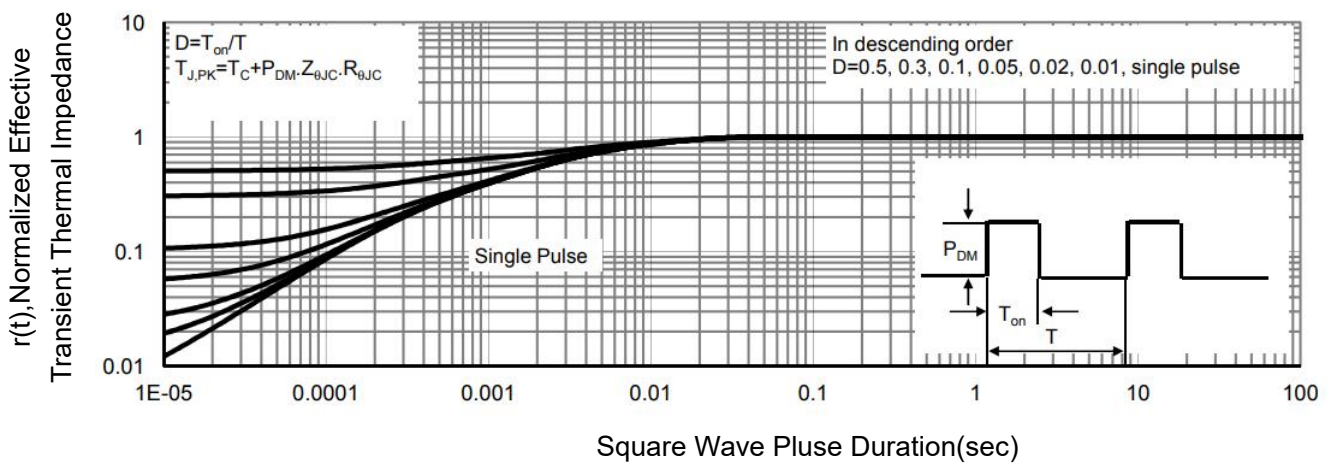
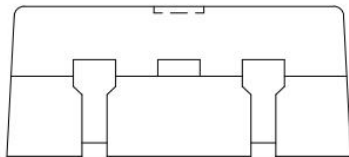
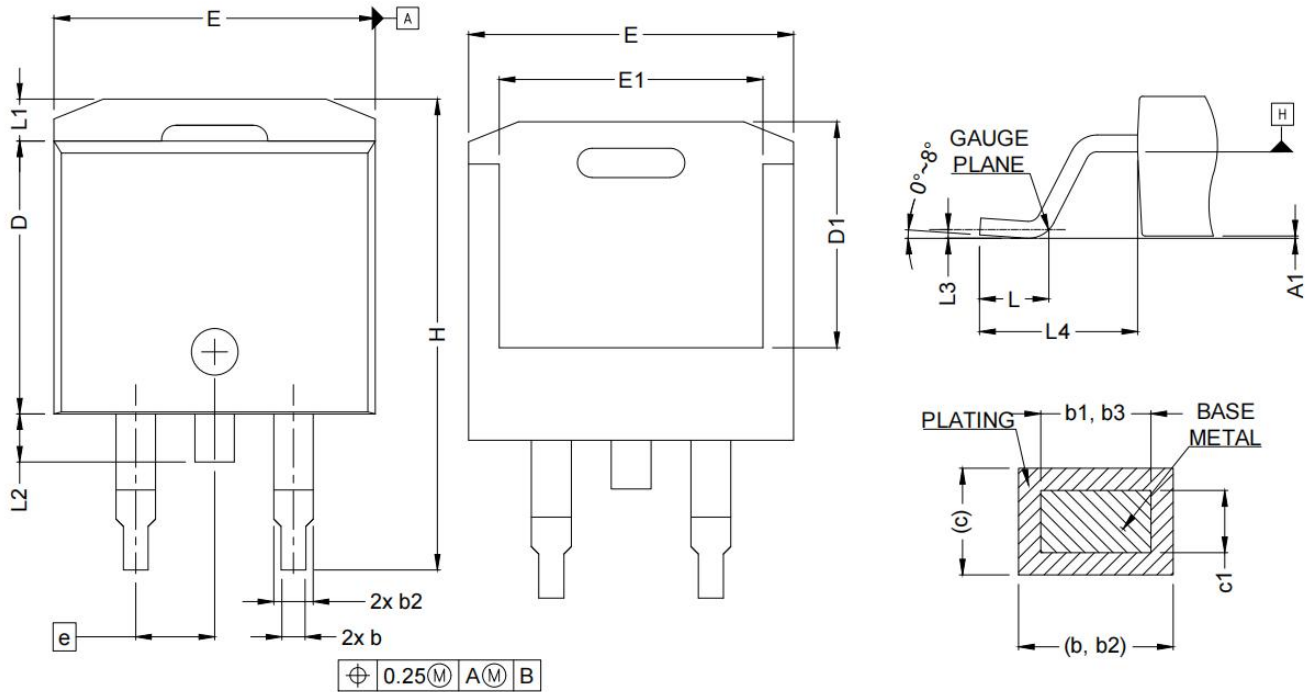


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263-2L Package Information



OPTION 1

2 LEADs

SYMBOL	MIN.	MAX.	SYMBOL	MIN.	MAX.
A	4.36	4.56	E	10.15	10.55
A1	0	0.25	E1	8.10	8.70
b	0.70	0.90	e	2.54 BSC	
b1	0.51	0.89	H	15.00	15.60
b2	1.17	1.37	L	1.90	2.50
b3	1.17	1.37	L1	-	1.65
c	0.38	0.69	L2	-	1.78
c1	0.38	0.53	L3	0.25 TYP	
c2	1.19	1.34	L4	4.78	5.28
D	8.60	9.00	J1	2.56	2.96
D1	6.90	7.50			

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